


Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1669		SERIAL NO. 09/921,518	
<div style="text-align: center;">  </div> <p style="text-align: center;">LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p>					APPLICANT: John T. Moore			
					FILING DATE August 1, 2001		GROUP 2818	
U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate		
PP ↑ ↓ PD	AA	3,622,319	11/23/71	Sharp	96	27		
	AB	3,743,847	07/03/73	Boland	250	510		
	AC	4,269,935	05/26/81	Masters et al.	430	323		
	AD	4,312,938	01/26/82	Drexler et al.	430	496		
	AE	4,320,191	03/16/82	Yoshikawa et al.	430	296		
	AF	4,795,657	01/03/89	Formigoni et al.	427	96		
	AG	4,847,674	07/11/89	Silwa et al.	357	67		
	AH	5,177,567	01/05/93	Klersy et al.	257	4		
	AI	5,219,788	06/15/93	Abernathey et al.	437	187		
PD	AJ	5,751,012	05/12/98	Wolstenholme et al.	257	5		
FOREIGN PATENT DOCUMENTS								
	Document Number	Date	Country	Class	Subclass	Translation		
						Yes	No	
	AK							
	AL							
	AM							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
PP ↑	AN	Das et al., <i>Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists</i> , 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989).						
↓ PD	AO	Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY pp. 24-29 (1982)						
↓ PD	AP	Hilt, DISSERTATION: <i>Materials Characterization of Silver Chalcogenide Programmable Metallization Cells</i> , Arizona State University, pp. title page-114 (UMI Company, May 1999).						
EXAMINER PHUC T. DANG				DATE CONSIDERED 5/28/04				
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								

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U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.
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SERIAL NO.
09/921,518



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(Use several sheets if necessary)

APPLICANT: John T. Moore

FILING DATE
August 1, 2001

**GROUP
2818**

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
PD	AA	5,789,277	08/04/98	Zahorik et al.	438	95	
	AB	5,841,150	11/24/98	Gonzalez et al.	257	3	
	AC	5,920,788	07/06/99	Reinberg	438	466	
	AD	5,998,066	12/07/99	Block et al.	430	5	
	AE	6,077,729	06/20/00	Harshfield	438	128	
	AF	6,236,059 B1	05/22/01	Wolstenholme et al.	257	3	
	AG	6,297,170 B1	10/02/01	Gabriel et al.	438	738	
	AH	6,300,684 B1	10/09/01	Gonzalez et al.	257	774	
	AI	6,316,784 B1	11/13/01	Zahorik et al.	257	3	
	AJ	6,329,606 B1	12/11/01	Freyman et al.	174	260	
PD	AK	6,348,365	02/19/02	Moore et al.	438	130	

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

PD ↑	AN		Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAMIC SOC., Nos. 3-4, pp. 183-188 (Mar.-Apr. 1979).
	AO		Huggett et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆</i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).
↓ PD	AP		Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).

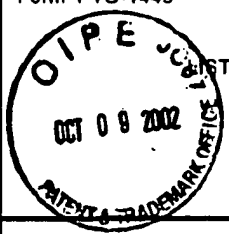
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PHUC T. DANG

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PD ↑ ↓ PD	AA	6,376,284 B1	04/23/02	Gonzalez et al.	438	129	
	AB	6,391,688 B1	05/21/02	Gonzalez et al.	438	128	
	AC	6,414,376 B1	07/02/02	Thakur et al.	257	640	
	AD	6,418,049 B1	07/09/02	Kozicki et al.	365	174	
	AE	6,423,628 B1	07/23/02	Li et al.	438	622	
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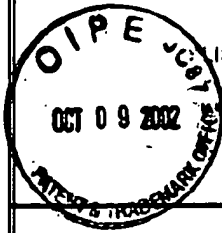
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PD ↑ ↓ PD	AN	McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation</i> , 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987).
	AO	Miyatani, <i>Electrical Properties of Ag₂Se</i> , 13 J. Phys. Soc. Japan, p. 317 (1958).
	AP	Mizusaki et al. <i>Kinetic Studies on the Selenization of Silver</i> , 47 BUL. CHEM. SOC. JAPAN., No. 11 pp. 2851-2855 (November 1974).

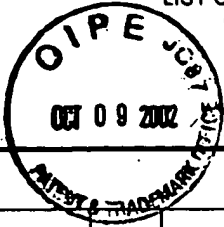
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PD	AA	10/061,825	Gilton et al. (as filed and amended)			01/31/2002		
PP	AB	10/077,867	Campbell et al. (as filed)			02/20/2002		
PD	AC	10/232,757	Li, et al. (as filed)			08/29/2002		
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PD ↑	AN		Owens et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (Academic Press, 1989).					
			Safran et al., <i>TEM study of Ag₂Se developed by the reaction of polycrystalline silver films and selenium</i> , 317 THIN SOLID FILMS, pp. 72-76 (1998).					
↓ PD	AP		Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 BUL. CHEM. SOC. JAPAN, No. 12, pp. 3662-3665 (December 1973).					
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							Yes No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
PD ↑ ↓ PD	AN		Somogyi et al., <i>Temperature Dependence of the Carrier Mobility in Ag₂Se Layers Grown on NaCl and SiO₂ Substrates</i> , 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255 (1994).				
	AO		Tai et al., <i>Multilevel Ge-Se film based resist systems</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 32-39 (March 1982).				
AP		Tai et al., <i>Submicron optical lithography using an inorganic resist/polymer bilevel scheme</i> ,					
		17 J. Vac. Sci. Technol., No. 5, pp. 1169-1176 (Sept./Oct. 1980).					
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PD ↑ ↓ PD	AN		West, DISSERTATION: <i>Electrically Erasable Non-Volatile Memory Via electrochemical Deposition of Multifractal Aggregates</i> , Arizona State University, pp. title page-168 (UMI Co., May 1998).				
	AO		West et al., <i>Equivalent Circuit Modeling of the Ag(As_{0.24}S_{0.38}Ag_{0.40})Ag System Prepared by Photodissolution of Ag</i> , 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (September 1998).				
AP		Yoshikawa et al., <i>A new inorganic electron resist of high contrast</i> , 31 APPL. PHYS. LETT., No. 3, pp. 161-163 (August 1977).					
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PD	AN		Yoshikawa et al., <i>Dry development of Se-Ge Inorganic photoresist</i> , 36 APPL. PHYS. LETT., No. 1,				
			pp. 107-109 (January 1980).				
	AO						
	AP						
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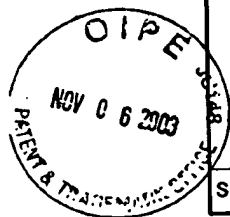
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 8

Compl 1 If Known

Application Number	09/921,518
Filing Date	August 1, 2001
First Named Inventor	John T. Moore
Art Unit	2818
Examiner Name	Phuc T. Dang
Attorney Docket Number	M4065.0696/P696



U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
PP ↑	AA	5,761,115	06/02/1998	Kozicki et al.	
	AB	6,084,796	07/04/2000	Kozicki et al.	
	AC	5,914,893	06/22/1999	Kozicki et al.	
	AD	5,896,312	04/20/1999	Kozicki et al.	
	AE	6,388,324	05/14/2002	Kozicki et al.	
↓	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
PD	AG	5,500,532	03/19/1996	Kozicki et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
PD	BA	WO 02/21542	03/14/2002	Kozicki et al.		
↑	BB	WO 00/48196	08/17/2000	Kozicki et al.		
	BC	WO 97/48032	12/18/1997	Kozicki et al.		
PD	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner
Signature

PHUC T. DANG

Date
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 601.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.



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		Filing Date	August 1, 2001	
		First Named Inventor	John T. Moore	
		Group Art Unit	2818	
		Examiner Name	Phuc T. Dang	
Sheet	2	8	Attorney Docket Number	M4065.0696/P696

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
PP	CA	Abdel-Ail, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.		
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge _{25-x} Sb _x , Appl. Phys. A 55 (1992) 167-169.		
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.		
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
	CH	Angeli, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.		
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810.		
	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
	CM	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.		
	CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag ₇ GeSe ₅ I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.		
	CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.		
	CP	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, Thin solid films 70 (1980) L1-L4.		
	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.		
	CR	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.		
	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.		
	CT	Bernede, J.C.; Conan, A.; Fousenan, E.; El Bouchaïri, B.; Goureaux, G., Polarized memory switching effects in Ag ₂ Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.		
	CU	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.		
	CV	Bondarev, V.N.; Pikhitsa, P.V., A dndrit model of current instability in RbAg ₄ I ₅ , Solid Stat Ionics 70/71 (1994) 72-76.		
PD	CW	Boochand, P., Th maximum in glass transition temperature (Tg) n ar x=1/3 In GexSe _{1-x}		

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PHUC T. DANG

PRIMARY EXAMINER

Phuc T. Dang

5/28/04



PTO/SB/088 (10-01)

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PD		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CB1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe2 glass, Phys. Rev. B 25 (1982) 2975-2978.	
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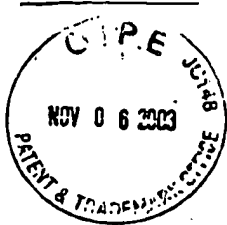
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				Application Number	09/921,518	Conf.#6082
				Filing Date	August 1, 2001	
				First Named Inventor	John T. Moore	
				Art Unit	2818	
				Examiner Name	P. Dang	
Sheet	1	of	3	Attorney Docket Number	M4065.0696/P696	

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				First Named Inventor	John T. Moore
				Art Unit	2818
				Examiner Name	P. Dang
				Attorney Docket Number	M4065.0696/P696
Sheet	2	of	3		

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		Filing Date	August 1, 2001		
		First Named Inventor	John T. Moore		
		Group Art Unit	2818		
		Examiner Name	P. Dang		
Sheet	3	of	3	Attorney Docket Number	M4065.0696/P696

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Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
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				Examiner Name	P. T. Dang
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